


“High Side Chopper” IGBT SOT-227, 70 A



SOT-227

FEATURES

- Trench IGBT technology
- Higher switching frequency up to 150 kHz
- Square RBSOA
- Low $V_{CE(on)}$
- FRED Pt[®] hyperfast rectifier
- Fully isolated package
- Very low internal inductance (≤ 5 nH typical)
- Industry standard outline
- UL approved file E78996 
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912



RoHS
COMPLIANT

PRIMARY CHARACTERISTICS

V_{CES}	600 V
I_C DC	70 A at 57 °C
$V_{CE(on)}$ typical at 70 A, 25 °C	1.79 V
I_F DC	70 A at 86 °C
Package	SOT-227
Circuit configuration	High side chopper

BENEFITS

- Designed for increased operating efficiency in power conversion: UPS, SMPS, welding, induction heating
- Easy to assemble and parallel
- Direct mounting to heatsink
- Plug-in compatible with other SOT-227 packages
- Lower conduction losses and switching losses
- Low EMI, requires less snubbing

ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	TEST CONDITIONS	MAX.	UNITS
Collector to emitter voltage	V_{CES}		600	V
Continuous collector current	I_C	$T_C = 25$ °C	81	A
		$T_C = 80$ °C	61	
Pulsed collector current	I_{CM}		170	
Clamped inductive load current	I_{LM}		250	
Diode continuous forward current	I_F	$T_C = 25$ °C	113	
		$T_C = 80$ °C	75	
Single pulse forward current	I_{FSM}	10 ms sine or 6 ms rectangular pulse, $T_J = 25$ °C	390	
Gate to emitter voltage	V_{GE}		± 20	V
Power dissipation, IGBT	P_D	$T_C = 25$ °C	231	W
		$T_C = 80$ °C	146	
Power dissipation, diode	P_D	$T_C = 25$ °C	330	
		$T_C = 80$ °C	179	
RMS isolation voltage	V_{ISOL}	Any terminal to case, $t = 1$ min	2500	V



ELECTRICAL SPECIFICATIONS ($T_J = 25\text{ }^\circ\text{C}$ unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Collector to emitter breakdown voltage	$V_{BR(CES)}$	$V_{GE} = 0\text{ V}, I_C = 0.4\text{ mA}$	600	-	-	V
Collector to emitter voltage	$V_{CE(on)}$	$V_{GE} = 15\text{ V}, I_C = 35\text{ A}$	-	1.44	-	
		$V_{GE} = 15\text{ V}, I_C = 70\text{ A}$	-	1.79	2.26	
		$V_{GE} = 15\text{ V}, I_C = 35\text{ A}, T_J = 125\text{ }^\circ\text{C}$	-	1.60	-	
		$V_{GE} = 15\text{ V}, I_C = 70\text{ A}, T_J = 125\text{ }^\circ\text{C}$	-	2.02	-	
Gate threshold voltage	$V_{GE(th)}$	$V_{CE} = V_{GE}, I_C = 0.6\text{ mA}$	2.9	3.9	5.1	
Temperature coefficient of threshold voltage	$\Delta V_{GE(th)}/\Delta T_J$	$V_{CE} = V_{GE}, I_C = 0.6\text{ mA}$ (25 °C to 125 °C)	-	-10.0	-	mV/°C
Collector to emitter leakage current	I_{CES}	$V_{GE} = 0\text{ V}, V_{CE} = 600\text{ V}$	-	0.2	100	μA
		$V_{GE} = 0\text{ V}, V_{CE} = 600\text{ V}, T_J = 125\text{ }^\circ\text{C}$	-	19	-	
Diode reverse breakdown voltage	V_{BR}	$I_R = 1\text{ mA}$	600	-	-	V
Diode forward voltage drop	V_{FM}	$I_F = 35\text{ A}, V_{GE} = 0\text{ V}$	-	1.67	2.33	V
		$I_F = 70\text{ A}, V_{GE} = 0\text{ V}$	-	1.96	-	
		$I_F = 35\text{ A}, V_{GE} = 0\text{ V}, T_J = 125\text{ }^\circ\text{C}$	-	1.23	-	
		$I_F = 70\text{ A}, V_{GE} = 0\text{ V}, T_J = 125\text{ }^\circ\text{C}$	-	1.55	-	
Diode reverse leakage current	I_{RM}	$V_R = 600\text{ V}$	-	0.1	50	μA
		$T_J = 125\text{ }^\circ\text{C}, V_R = 600\text{ V}$	-	0.04	-	mA
Gate to emitter leakage current	I_{GES}	$V_{GE} = \pm 20\text{ V}$	-	-	± 200	nA

SWITCHING CHARACTERISTICS ($T_J = 25\text{ }^\circ\text{C}$ unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Total gate charge (turn-on)	Q_g	$I_C = 70\text{ A}, V_{CC} = 520\text{ V}, V_{GE} = 15\text{ V}$	-	193	-	nC	
Gate to emitter charge (turn-on)	Q_{ge}		-	29	-		
Gate to collector charge (turn-on)	Q_{gc}		-	56	-		
Turn-on switching loss	E_{on}	$I_C = 35\text{ A}, V_{CC} = 300\text{ V}, V_{GE} = 15\text{ V}, R_g = 4.7\text{ }\Omega, L = 500\text{ }\mu\text{H}, T_J = 25\text{ }^\circ\text{C}$	-	0.35	-	mJ	
Turn-off switching loss	E_{off}		-	0.15	-		
Total switching loss	E_{tot}		-	0.5	-		
Turn-on switching loss	E_{on}	$I_C = 70\text{ A}, V_{CC} = 300\text{ V}, V_{GE} = 15\text{ V}, R_g = 4.7\text{ }\Omega, L = 500\text{ }\mu\text{H}, T_J = 25\text{ }^\circ\text{C}$	-	0.8	-		
Turn-off switching loss	E_{off}		-	0.34	-		
Total switching loss	E_{tot}		-	1.14	-		
Turn-on switching loss	E_{on}	$I_C = 35\text{ A}, V_{CC} = 300\text{ V}, V_{GE} = 15\text{ V}, R_g = 4.7\text{ }\Omega, L = 500\text{ }\mu\text{H}, T_J = 125\text{ }^\circ\text{C}$	-	0.56	-		ns
Turn-off switching loss	E_{off}		-	0.25	-		
Total switching loss	E_{tot}		-	0.81	-		
Turn-on delay time	$t_{d(on)}$	Energy losses include tail and diode recovery	-	24	-		
Rise time	t_r		-	9	-		
Turn-off delay time	$t_{d(off)}$		-	105	-		
Fall time	t_f	-	31	-			
Turn-on switching loss	E_{on}	$I_C = 70\text{ A}, V_{CC} = 300\text{ V}, V_{GE} = 15\text{ V}, R_g = 4.7\text{ }\Omega, L = 500\text{ }\mu\text{H}, T_J = 125\text{ }^\circ\text{C}$	-	0.95	-	mJ	
Turn-off switching loss	E_{off}		-	0.53	-		
Total switching loss	E_{tot}		-	1.48	-		
Turn-on delay time	$t_{d(on)}$	Energy losses include tail and diode recovery	-	26	-	ns	
Rise time	t_r		-	23	-		
Turn-off delay time	$t_{d(off)}$		-	101	-		
Fall time	t_f	-	24	-			
Reverse bias safe operating area	RBSOA	$T_J = 175\text{ }^\circ\text{C}, I_C = 250\text{ A}, R_g = 4.7\text{ }\Omega, V_{GE} = 15\text{ V to } 0\text{ V}, V_{CC} = 300\text{ V}, V_P = 600\text{ V}$	Fullsquare				
Diode reverse recovery time	t_{rr}	$I_F = 50\text{ A}, dI_F/dt = 200\text{ A}/\mu\text{s}, V_R = 200\text{ V}$	-	64	-	ns	
Diode peak reverse current	I_{rr}		-	4.5	-	A	
Diode recovery charge	Q_{rr}		-	144	-	nC	
Diode reverse recovery time	t_{rr}	$I_F = 50\text{ A}, dI_F/dt = 200\text{ A}/\mu\text{s}, V_R = 200\text{ V}, T_J = 125\text{ }^\circ\text{C}$	-	136	-	ns	
Diode peak reverse current	I_{rr}		-	12	-	A	
Diode recovery charge	Q_{rr}		-	807	-	nC	



THERMAL AND MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Junction and storage temperature range	T_J, T_{Stg}		-40	-	175	°C
Junction to case	IGBT		-	-	0.65	°C/W
	Diode		-	-	0.53	
Case to heatsink	R_{thCS}	Flat, greased surface	-	0.05	-	
Weight			-	30	-	g
Mounting torque		Torque to terminal	-	-	1.1 (9.7)	Nm (lbf.in)
		Torque to heatsink	-	-	1.3 (11.5)	Nm (lbf.in)
Case style		SOT-227				

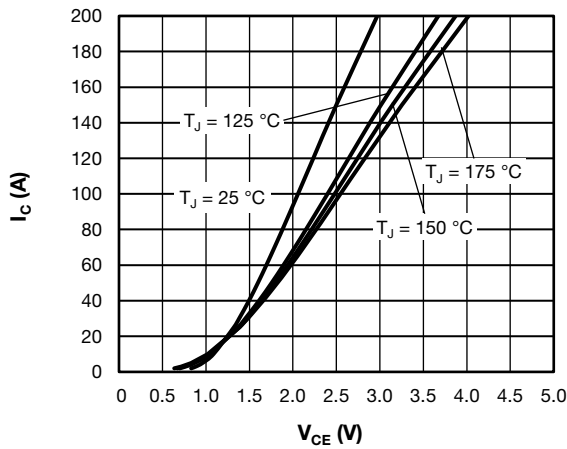


Fig. 1 - Typical Trench IGBT Output Characteristics, $V_{GE} = 15\text{ V}$

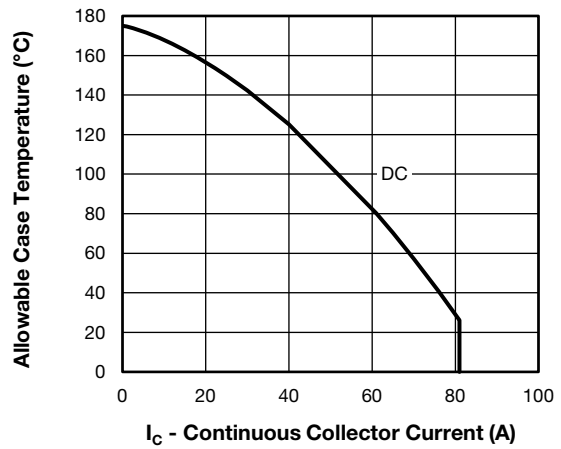


Fig. 3 - Maximum Trench IGBT Continuous Collector Current vs. Case Temperature

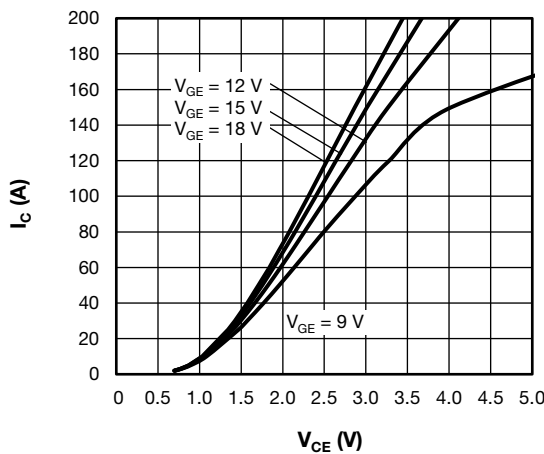


Fig. 2 - Typical Trench IGBT Output Characteristics, $T_J = 125\text{ °C}$

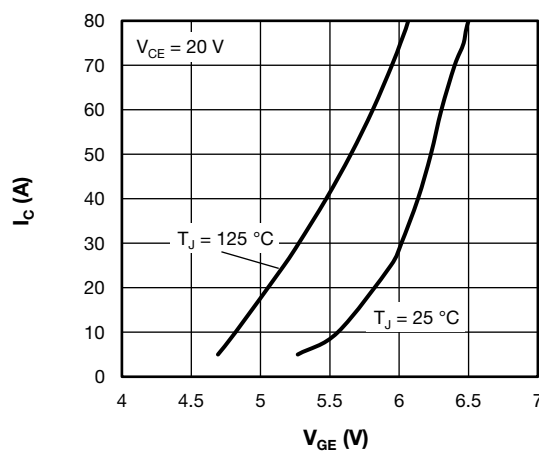


Fig. 4 - Typical Trench IGBT Transfer Characteristics

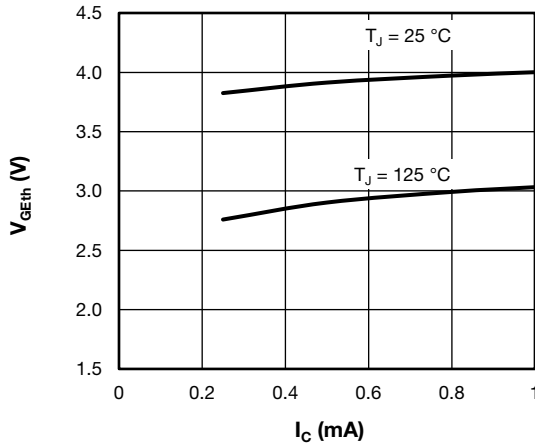


Fig. 5 - Typical Trench IGBT Gate Threshold Voltage

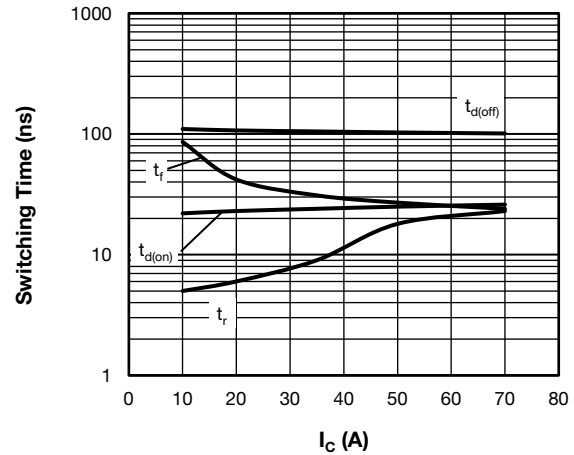


Fig. 8 - Typical Trench IGBT Switching Time vs. I_c
(with Antiparallel Diode)

$T_J = 125\text{ °C}$, $V_{CC} = 300\text{ V}$, $R_g = 4.7\ \Omega$, $V_{GE} = +15\text{ V}/-15\text{ V}$, $L = 500\ \mu\text{H}$

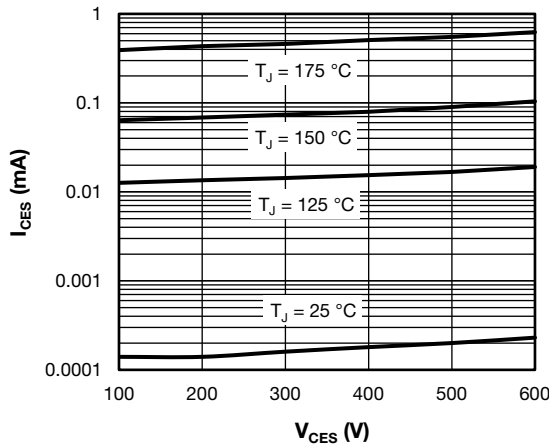


Fig. 6 - Typical Trench IGBT Zero Gate Voltage Collector Current

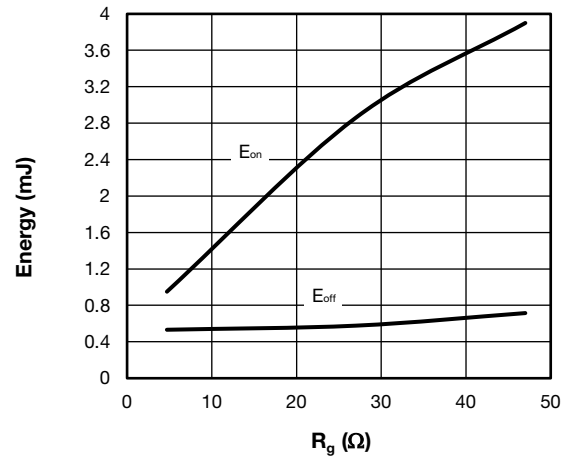


Fig. 9 - Typical Trench IGBT Energy Loss vs. R_g
(with Antiparallel Diode)

$T_J = 125\text{ °C}$, $V_{CC} = 300\text{ V}$, $I_c = 70\text{ A}$, $V_{GE} = +15\text{ V}/-15\text{ V}$, $L = 500\ \mu\text{H}$

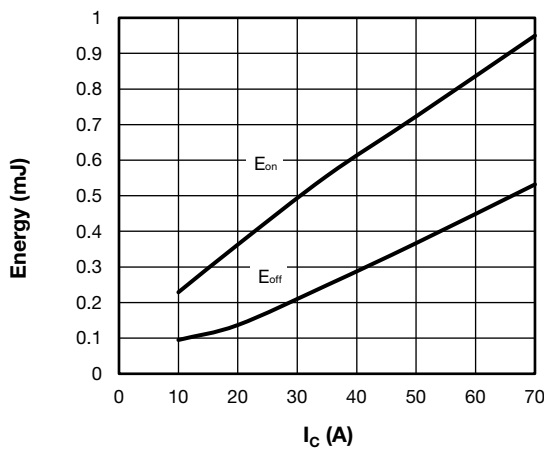


Fig. 7 - Typical Trench IGBT Energy Loss vs. I_c
(with Antiparallel Diode)

$T_J = 125\text{ °C}$, $V_{CC} = 300\text{ V}$, $R_g = 4.7\ \Omega$, $V_{GE} = +15\text{ V}/-15\text{ V}$, $L = 500\ \mu\text{H}$

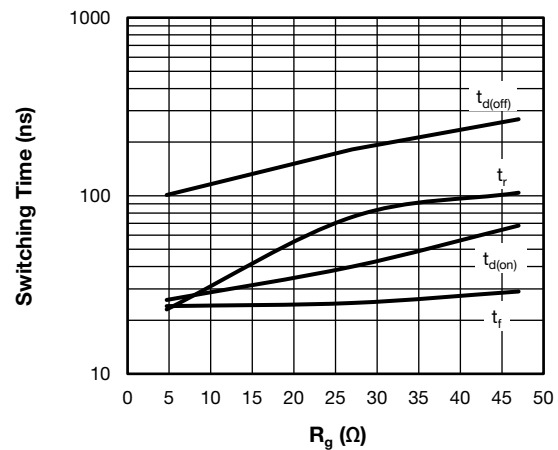


Fig. 10 - Typical Trench IGBT Switching Time vs. R_g
(with Antiparallel Diode)

$T_J = 125\text{ °C}$, $V_{CC} = 300\text{ V}$, $I_c = 70\text{ A}$, $V_{GE} = +15\text{ V}/-15\text{ V}$, $L = 500\ \mu\text{H}$

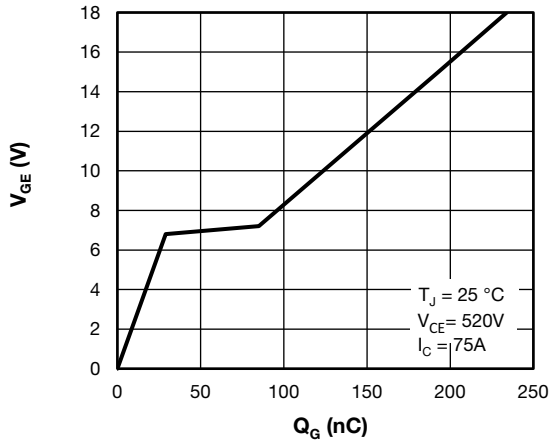


Fig. 11 - Typical Trench IGBT Gate Charge vs. Gate to Emitter Voltage

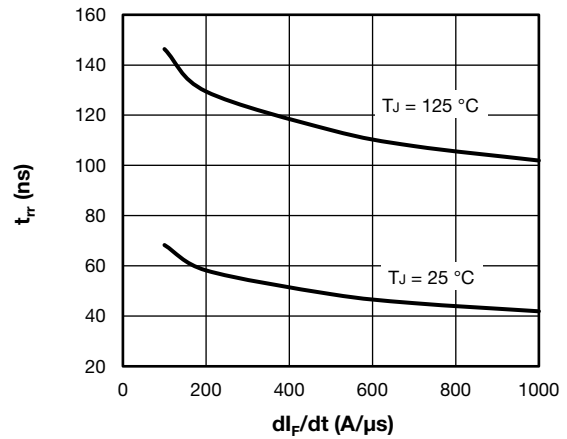


Fig. 14 - Typical Diode Reverse Recovery Time vs. dI_F/dt
 $I_F = 50 \text{ A}$, $V_{CC} = 200 \text{ V}$

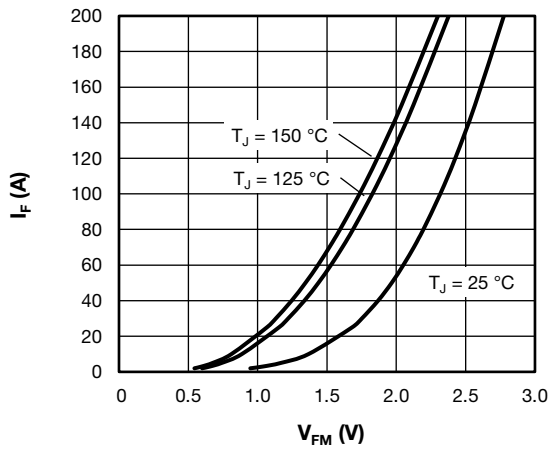


Fig. 12 - Typical Diode Forward Characteristics

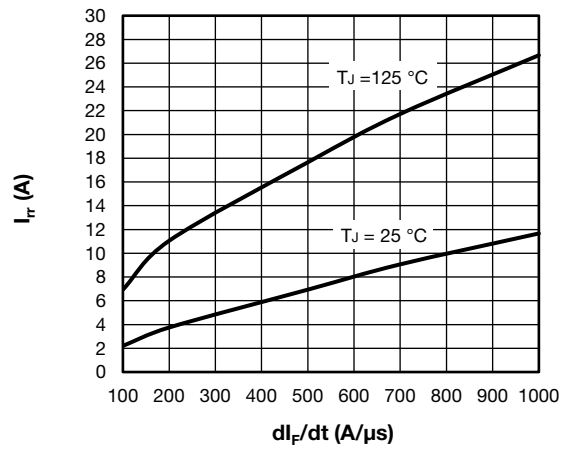


Fig. 15 - Typical Diode Reverse Recovery Current vs. dI_F/dt
 $I_F = 50 \text{ A}$, $V_{CC} = 200 \text{ V}$

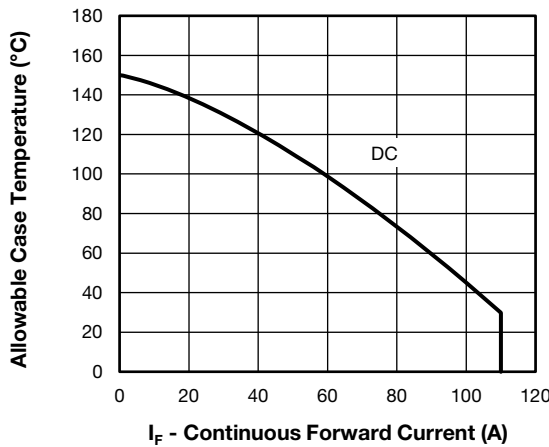


Fig. 13 - Maximum Diode Continuous Forward Current vs. Case Temperature

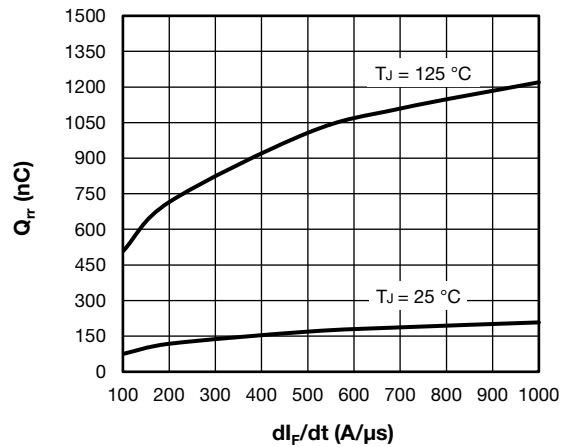


Fig. 16 - Typical Diode Reverse Recovery Charge vs. dI_F/dt
 $I_F = 50 \text{ A}$, $V_{CC} = 200 \text{ V}$

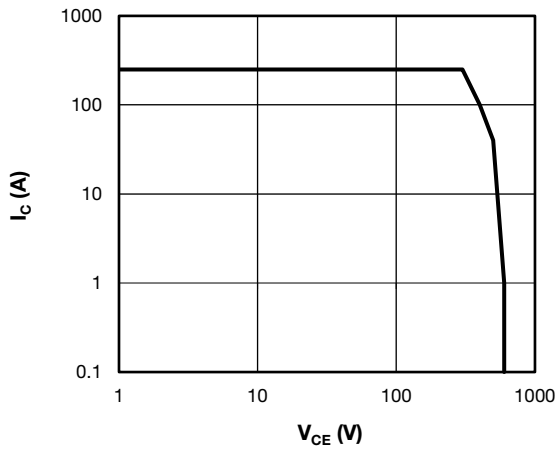


Fig. 17 - Trench IGBT Reverse BIAS SOA
 $T_J = 175\text{ }^\circ\text{C}$, $I_C = 250\text{ A}$, $R_g = 4.7\ \Omega$, $V_{GE} = +15\text{ V/0 V}$,
 $V_{CC} = 300\text{ V}$, $V_p = 600\text{ V}$

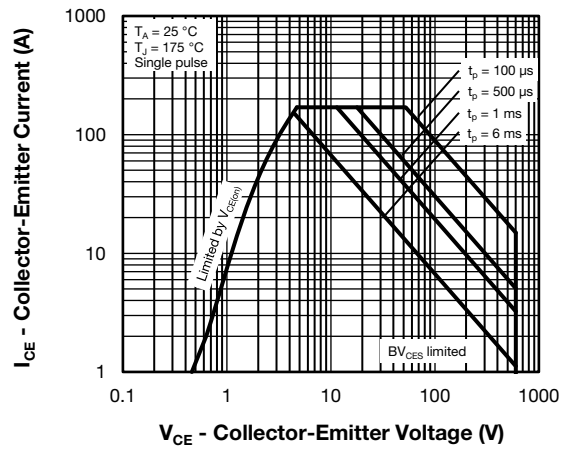


Fig. 18 - Trench IGBT Safe Operating Area

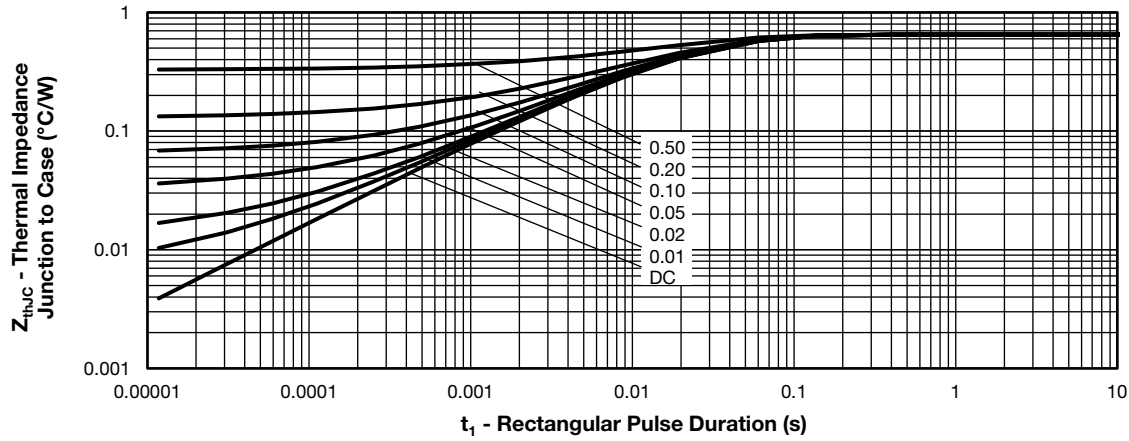


Fig. 19 - Maximum Trench IGBT Thermal Impedance Z_{thJC} Characteristics

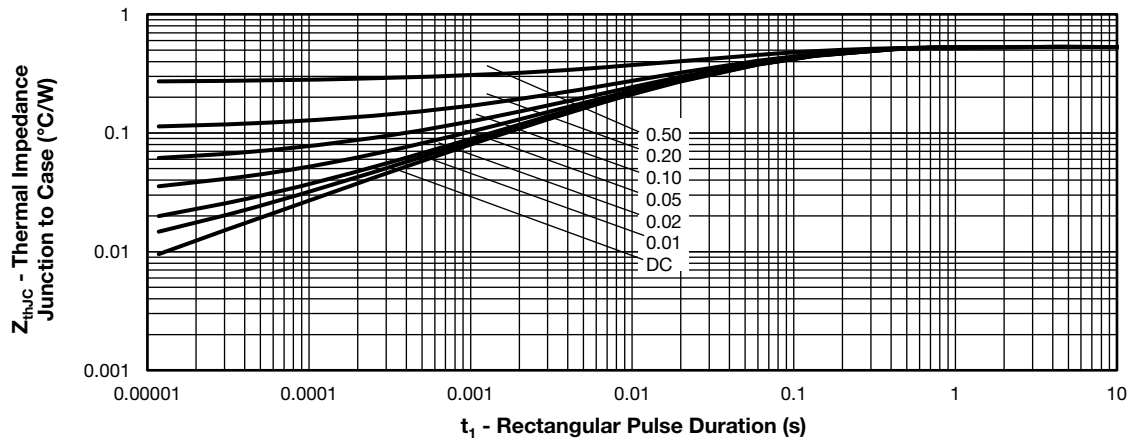


Fig. 20 - Maximum Diode Thermal Impedance Z_{thJC} Characteristics

ORDERING INFORMATION TABLE

Device code	VS-	G	T	75	N	A	60	U	F
	①	②	③	④	⑤	⑥	⑦	⑧	⑨
	1	2	3	4	5	6	7	8	9
	-	-	-	-	-	-	-	-	-
	Vishay Semiconductors product	Insulated gate bipolar transistor (IGBT)	T = Trench IGBT	Current rating (75 = 75 A)	Circuit configuration (N = high side chopper)	Package indicator (A = SOT-227)	Voltage rating (60 = 600 V)	Speed / type (U = ultrafast IGBT)	Diode (F = FRED Pt [®] diode)

CIRCUIT CONFIGURATION		
CIRCUIT	CIRCUIT CONFIGURATION CODE	CIRCUIT DRAWING
High side chopper	N	

LINKS TO RELATED DOCUMENTS	
Dimensions	www.vishay.com/doc?95423
Packaging information	www.vishay.com/doc?95425



SOT-227 Generation 2

DIMENSIONS in millimeters (inches)



Note

- Controlling dimension: millimeter



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